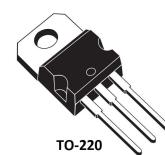
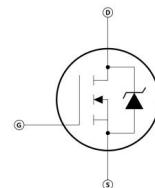


### Features

- 100% avalanche tested
- Avalanche ruggedness
- Very low intrinsic capacitances
- High speed switching
- Very low on-resistance



TO-220F



TO-220



TO-247

### Applications

- Welder
- UPS
- PV Inverter
- Switching applications

### Electrical ratings

Absolute maximum ratings			
Parameter	Symbol	Value	Unit
Drain-source voltage ( $V_{GS} = 0$ )	$V_{DS}$	1200	V
Gate- source voltage	$V_{GS}$	$\pm 20$	
Drain current (continuous) at $T_c = 25^\circ\text{C}$	$I_D$	6	A
Drain current (continuous) at $T_c = 100^\circ\text{C}$		3.8	
Drain current (pulsed)	$I_{DM}$	12	
Total dissipation at $T_c = 25^\circ\text{C}$ (TO-247/TO-220)	$P_{TOT}$	160	W
Total dissipation at $T_c = 25^\circ\text{C}$ (TO-220F)	$P_{TOT}$	33	W
Derating factor(TO-247/TO-220)		1.28	W/ $^\circ\text{C}$
Derating factor(TO-220F)		0.26	W/ $^\circ\text{C}$
Operating junction temperature	$T_J$	-55 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		

### Thermal data

Parameter	Symbol	Value		Unit
		TO-247	TO-220F	
Thermal resistance junction-case max	$R_{thj-case}$	0.78	3.79	W/ $^\circ\text{C}$
Thermal resistance junction-ambient max	$R_{thj-amb}$	76	84	
Maximum lead temperature for soldering purpose	$T_J$	300		

Avalanche characteristics				
Parameter	Symbol	Max value	Unit	
Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ max)	$I_{AR}$	2.1	A	
Single pulse avalanche energy (starting $T_J = 25^\circ C$ , $I_D = I_{AR}$ , $V_{DD} = 50 V$ )	$E_{AS}$	753	mJ	

**Electrical Characteristics ( $T_{vj} = 25^\circ C$  unless otherwise specified)**

On /off states							
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1 mA$ , $V_{GS} = 0$	1200			V	
Zero gate voltage drain current ( $V_{GS} = 0$ )	$I_{DSS}$	$V_{DS} = \text{Max rating}$ $V_{DS}=\text{Max rating}, T_C=125^\circ C$			66	$\mu A$	
Gate-body leakage current ( $V_{DS} = 0$ )	$I_{GSS}$	$V_{GS} = \pm 30 V$			$\pm 100$	nA	
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	3	4	5	V	
Static drain-source on resistance	$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 4A$		5.5	7	$\Omega$	
Dynamic							
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Forward transconductance	$g_{fs}$	$V_{DS} = 15 V$ , $I_D = 4$		5.7		S	
Input capacitance	$C_{iss}$	$V_{DS}=25V, f=1MHz, V_{GS}=0$		2310		pF	
Output capacitance	$C_{oss}$			330			
Reverse transfer capacitance	$C_{rss}$			80			
Equivalent Output capacitance	$C_{oss\text{ eq.}}$	$V_{GS}=0, V_{DS}=0$ to 1200V		120			
Gate input resistance	$R_g$	f=1MHz Gate DC Bias=0 Test signal level=20mV open drain		2.2		$\Omega$	
Total gate charge	$Q_g$	$V_{DD}=1200V, I_D=8A$ $V_{GS}=10V$		85		nC	
Gate-source charge	$Q_{gs}$			14			
Gate-drain charge	$Q_{gd}$			48			
Switching times							
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 750 V$ , $I_D = 4 A$ ,		33		ns	

Rise time	$t_r$	$R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$	26		
Turn-off-delay time	$t_{d(\text{off})}$		46		
Fall time	$t_f$		21		

### Source drain diode

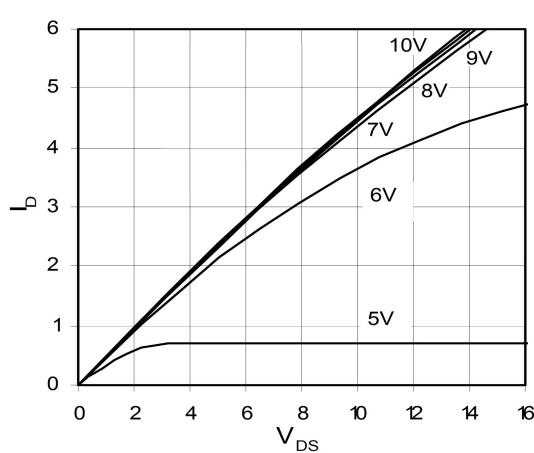
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Source-drain current	$I_{SD}$	$I_{SD} = 6 \text{ A}, V_{GS} = 0$		6		A
Source-drain current (pulsed)	$I_{SDM}$			12		
Forward on voltage	$V_{SD}$	$I_{SD} = 6 \text{ A}, V_{GS} = 0$		1.5		V
Reverse recovery time	$t_{rr}$	$I_{SD} = 6 \text{ A}, \text{di/dt} = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$		360		nS
Reverse recovery charge	$Q_{rr}$			5.3		$\mu\text{C}$
Reverse recovery current	$I_{RRM}$			19		A
Reverse recovery time	$t_{rr}$	$I_{SD} = 6 \text{ A}, \text{di/dt} = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ $T_J = 150^\circ\text{C}$		520		nS
Reverse recovery charge	$Q_{rr}$			7.6		$\mu\text{C}$
Reverse recovery current	$I_{RRM}$			17		A

### Order information

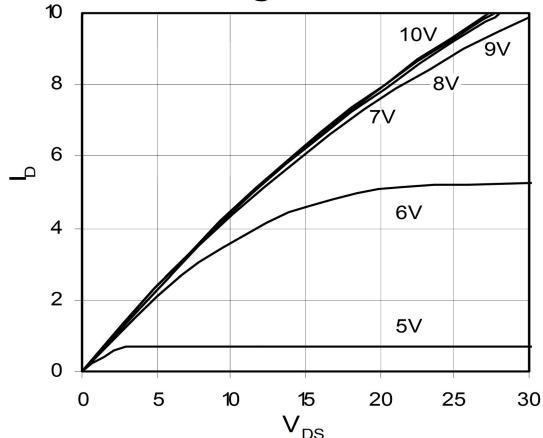
<b>MS6N120FS</b>	TO-220F	Tube	
<b>MS6N120FT</b>	TO-220	Tube	
<b>MS6N120FC</b>	TO-247	Tube	

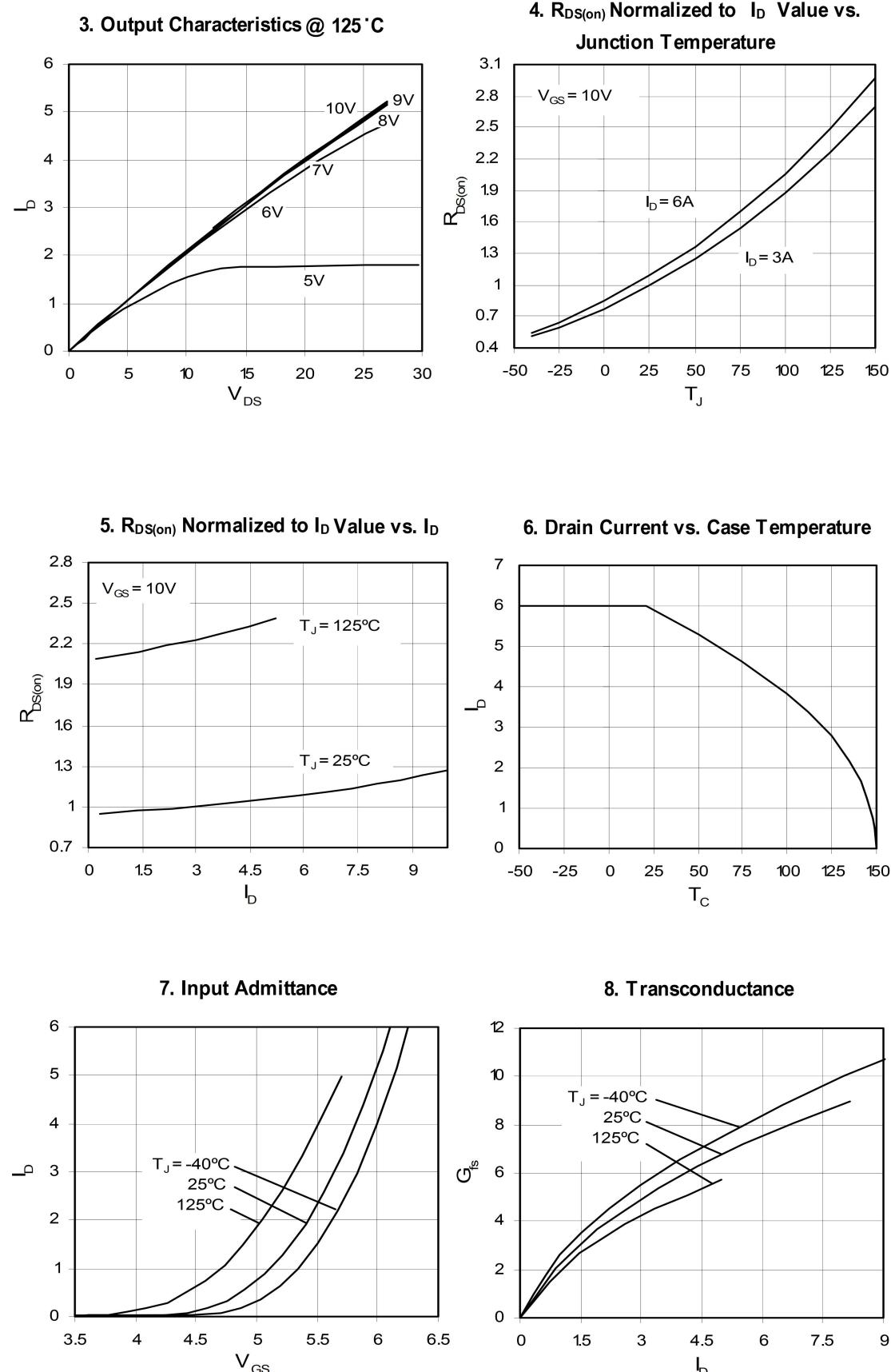
### Electrical characteristics

1. Output Characteristics @ 25°C

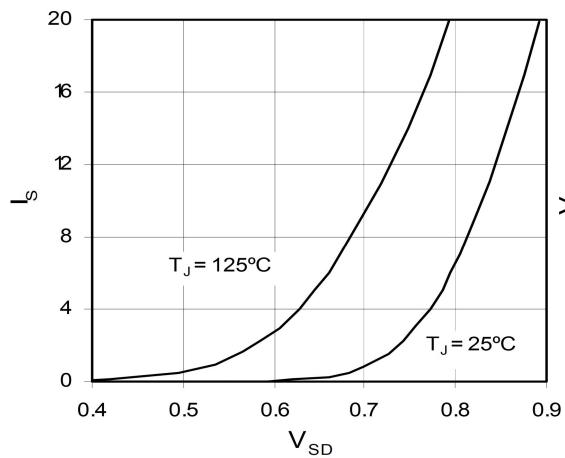


2. Extended Output Characteristics @ 25°C

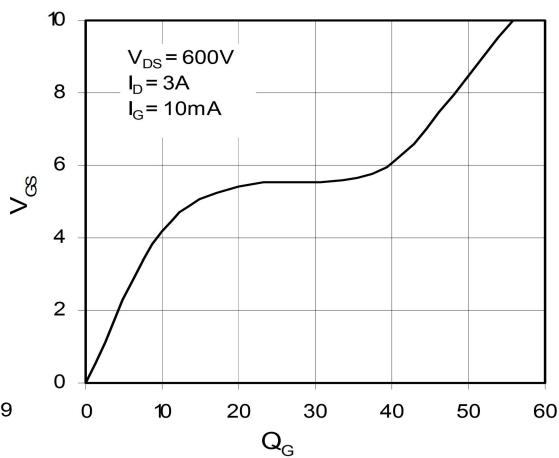




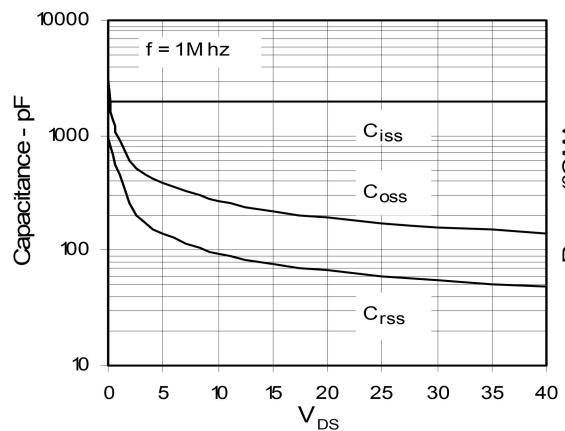
**9. Source Current vs. Source-To-Drain**



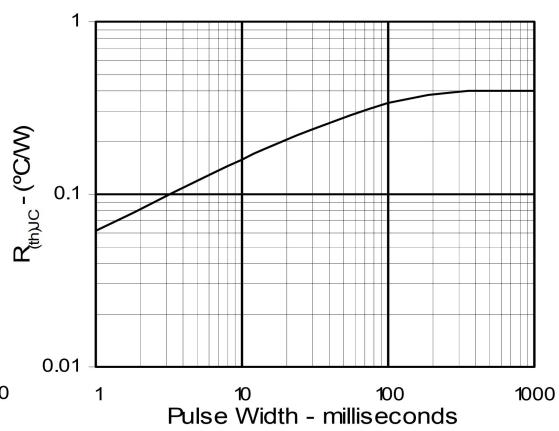
**10. Gate Charge**



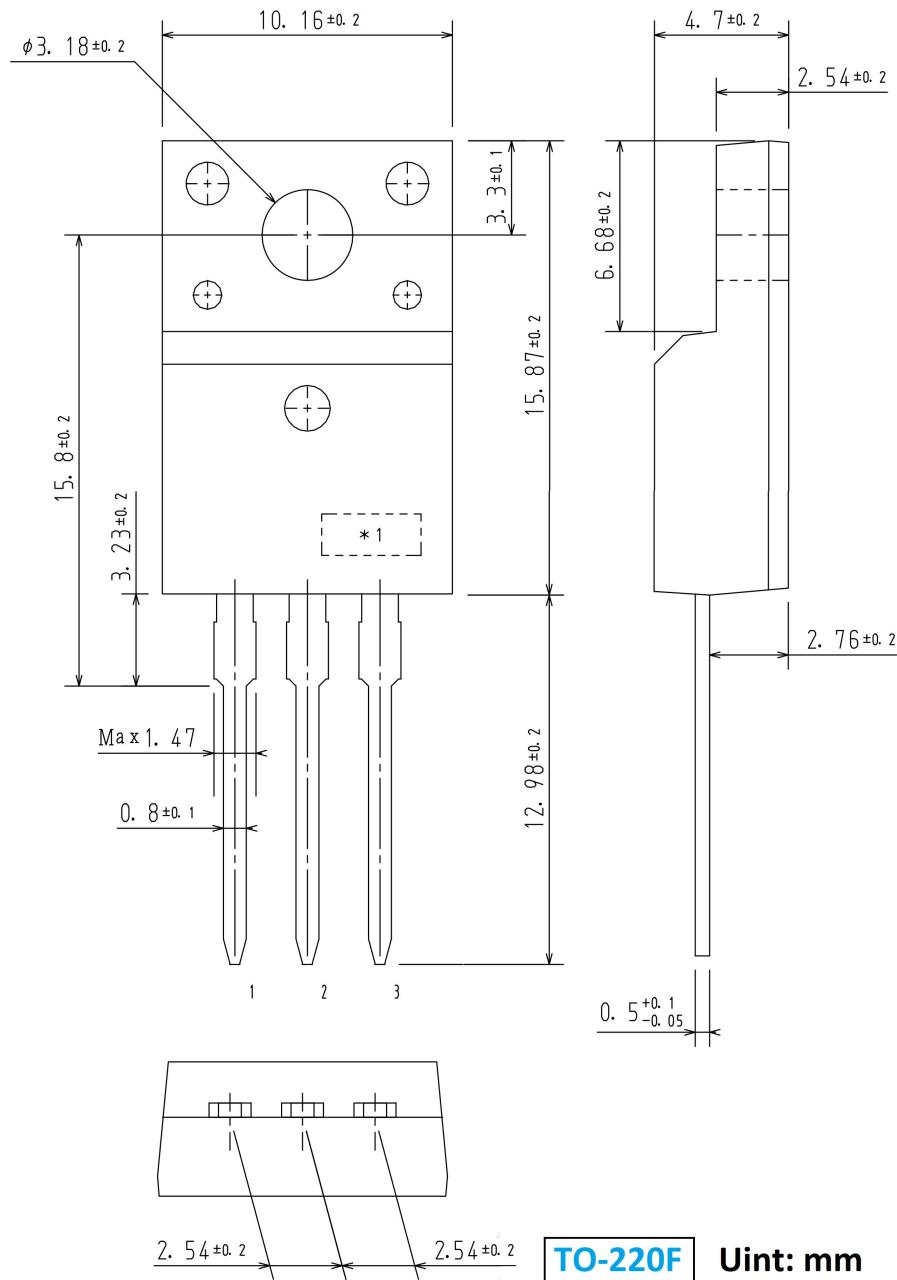
**11. Capacitance**



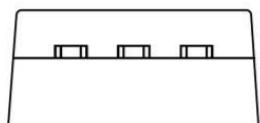
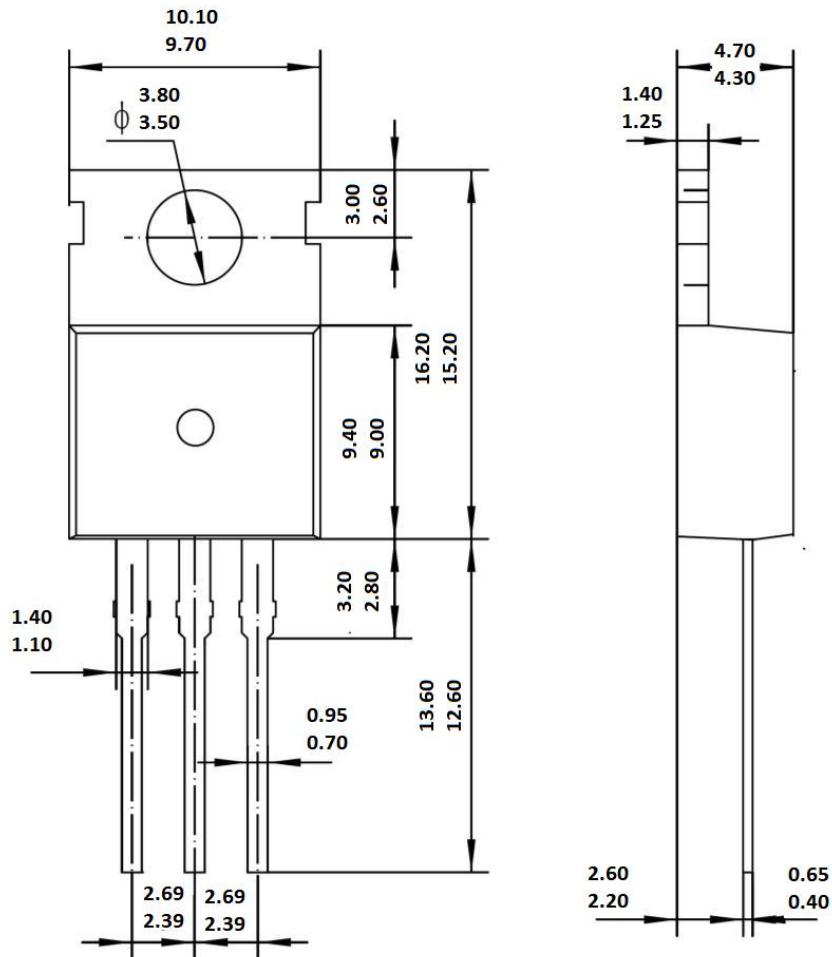
**12. Maximum Transient Thermal Resistance**



### Package outline dimension

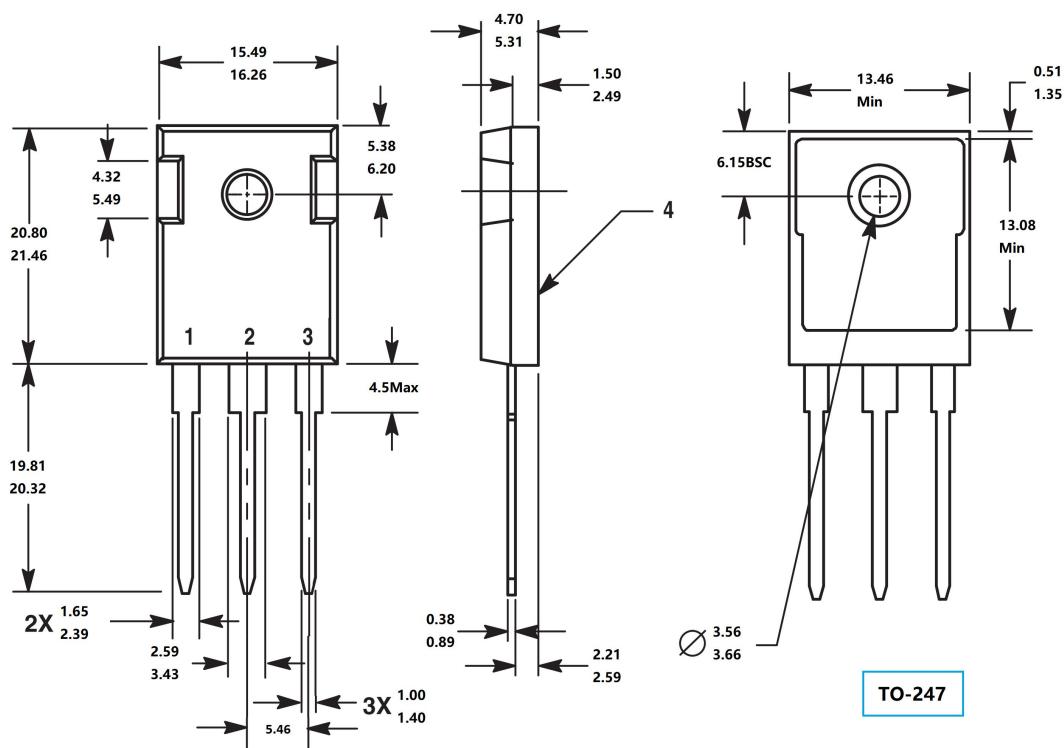


**TO-220F** **Uint: mm**



**TO-220**

**Unit: mm**



TO-247